

NTMFS5844NL, NVMFS5844NL

3. Surface-mounted on FR4 board using a 650 mm², 2 oz. Cu pad.
4. Maximum current for pulses as long as 1 second is higher but is dependent on pulse duration and duty cycle.

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0 V, I _D = 250 μA	60			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	V _{(BR)DSS} /T _J			57		mV/°C
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V, V _{DS} = 60 V	T _J = 25 °C		1	μA
			T _J = 125°C		100	
Gate-to-Source Leakage Current	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±20 V			±100	nA

ON CHARACTERISTICS (Note 5)

Gate Threshold Voltage	V _{GS(TH)}	V _{GS} = V _{DS} , I _D = 250 μA	1.5		2.3	V	
Negative Threshold Temperature Coefficient	V _{GS(TH)} /T _J			6.2		mV/°C	
Drain-to-Source On Resistance	R _{DS(on)}	V _{GS} = 10 V	I _D = 10 A		10.2	12	mΩ
		V _{GS} = 4.5 V	I _D = 10 A		13	16	
Forward Transconductance	g _{FS}	V _{DS} = 5 V, I _D = 10 A		27		S	

CHARGES, CAPACITANCES & GATE RESISTANCE

Input Capacitance	C _{ISS}	V _{GS} = 0 V, f = 1 MHz, V _{DS} = 25 V		1460		pF
Output Capacitance	C _{OSS}			150		
Reverse Transfer Capacitance	C _{RSS}			96		
Total Gate Charge	Q _{G(TOT)}	V _{GS} = 10 V, V _{DS} = 48 V; I _D = 10 A		30		nC
Total Gate Charge	Q _{G(TOT)}	V _{GS} = 4.5 V, V _{DS} = 48 V; I _D = 10 A		15		
Threshold Gate Charge	Q _{G(TH)}			1.0		
Gate-to-Source Charge	Q _{GS}			4.0		
Gate-to-Drain Charge	Q _{GD}			8.0		
Plateau Voltage	V _{GP}			3.0		
Gate Resistance	R _G			0.62		Ω

SWITCHING CHARACTERISTICS (Note 6)

Turn-On Delay Time	t _{d(ON)}	V _{GS} = 4.5 V, V _{DS} = 48 V, I _D = 10 A, R _G = 2.5 Ω		12		ns
Rise Time	t _r			25		
Turn-Off Delay Time	t _{d(OFF)}			20		
Fall Time	t _f			10		

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V _{SD}	V _{GS} = 0 V, I _S = 10 A	T _J = 25°C	0.79	1.2	V
			T _J = 125°C	0.65		
Reverse Recovery Time	t _{RR}	V _{GS} = 0 V, dI _S /dt = 100 A/μs, I _S = 10 A		19		ns
Charge Time	t _a			13		
Discharge Time	t _b			6.0		
Reverse Recovery Charge	Q _{RR}			15		

5. Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%.
6. Switching characteristics are independent of operating junction temperatures.

TYPICAL CHARACTERISTICS

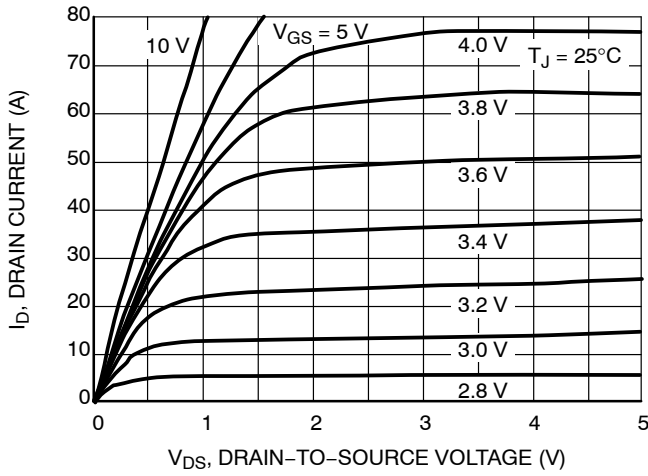


Figure 1. On-Region Characteristics

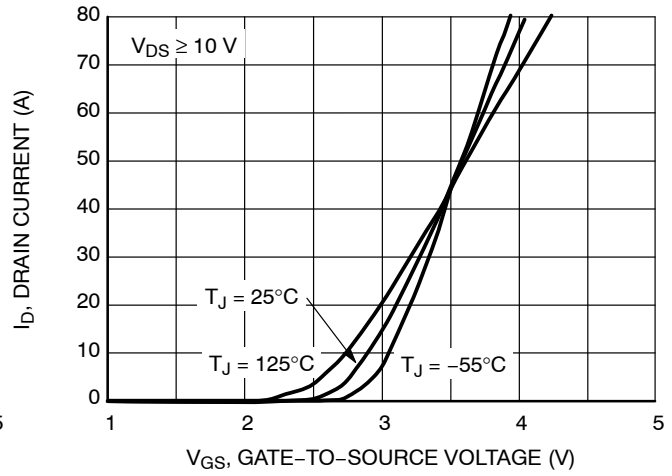


Figure 2. Transfer Characteristics

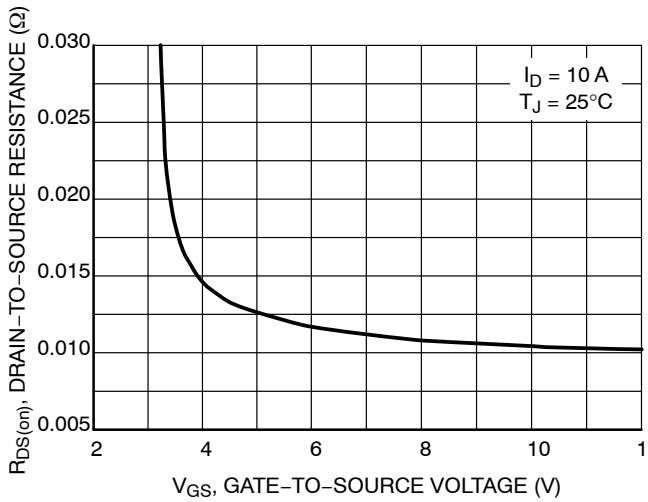


Figure 3. On-Resistance vs. Gate-to-Source Voltage

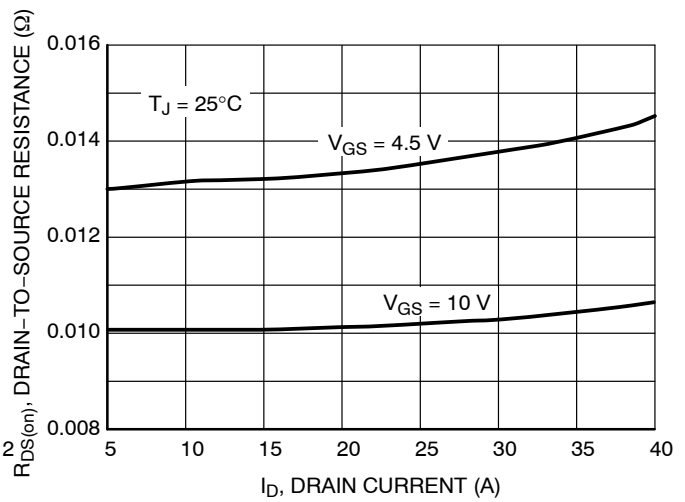


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

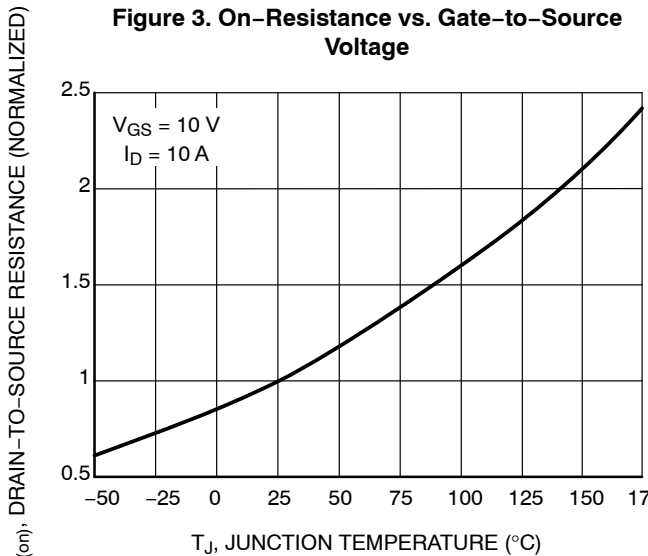


Figure 5. On-Resistance Variation with Temperature

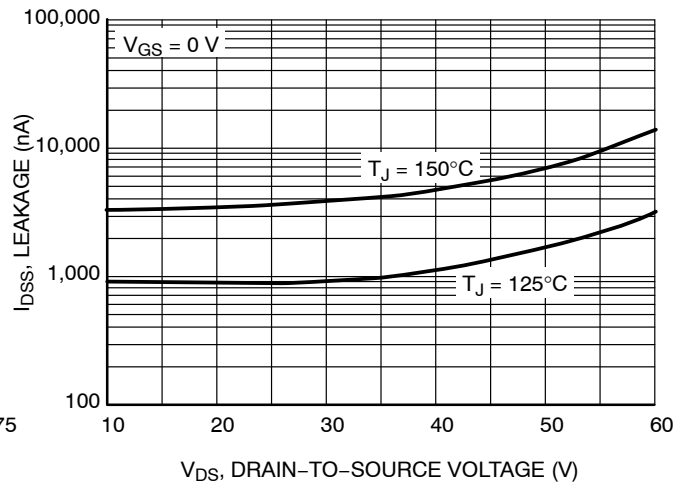


Figure 6. Drain-to-Source Leakage Current vs. Voltage

TYPICAL CHARACTERISTICS

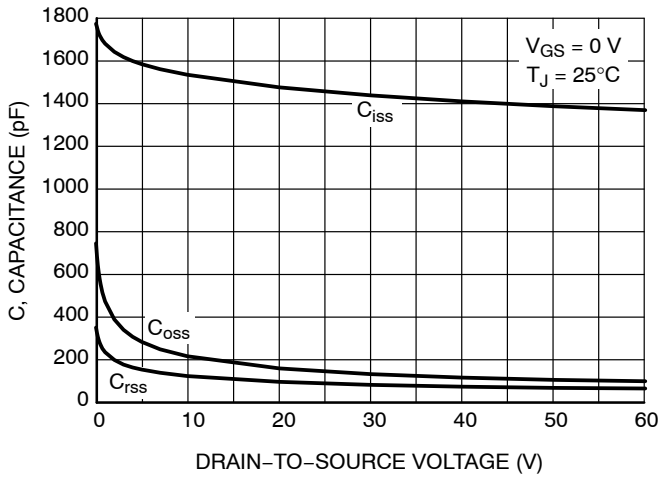


Figure 7. Capacitance Variation

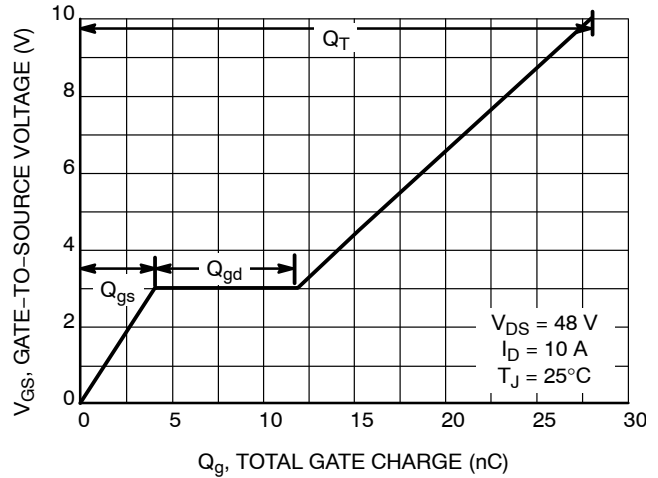


Figure 8. Gate-to-Source Voltage vs. Total Charge

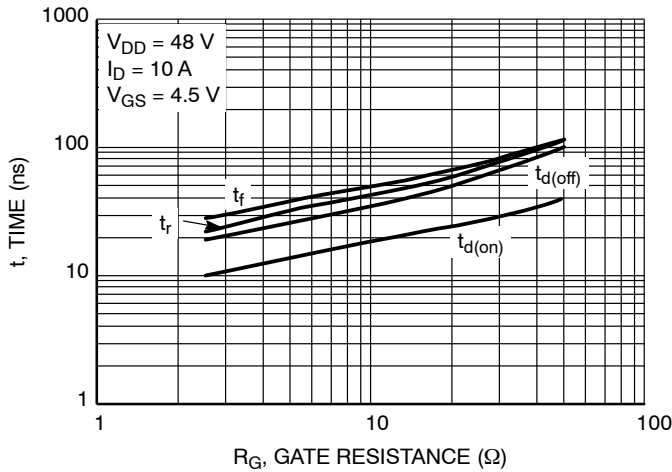


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

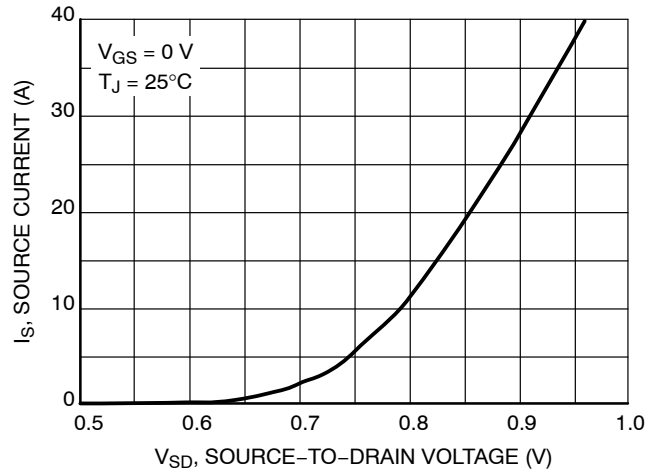


Figure 10. Diode Forward Voltage vs. Current

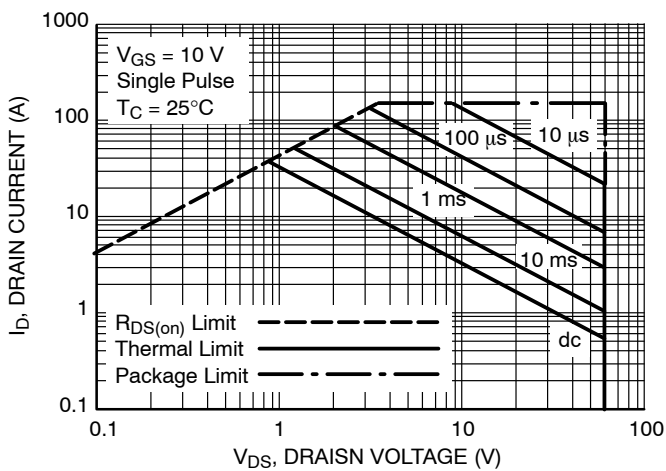


Figure 11. Maximum Rated Forward Biased Safe Operating Area

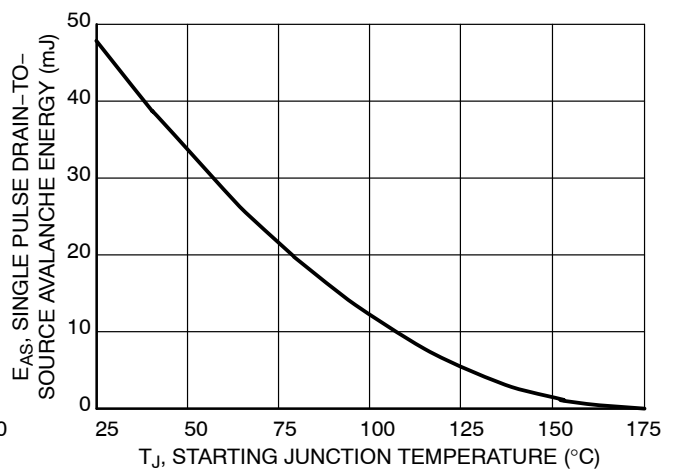


Figure 12. Maximum Avalanche Energy vs. Starting Junction Temperature

NTMFS5844NL, NVMFS5844NL

TYPICAL CHARACTERISTICS

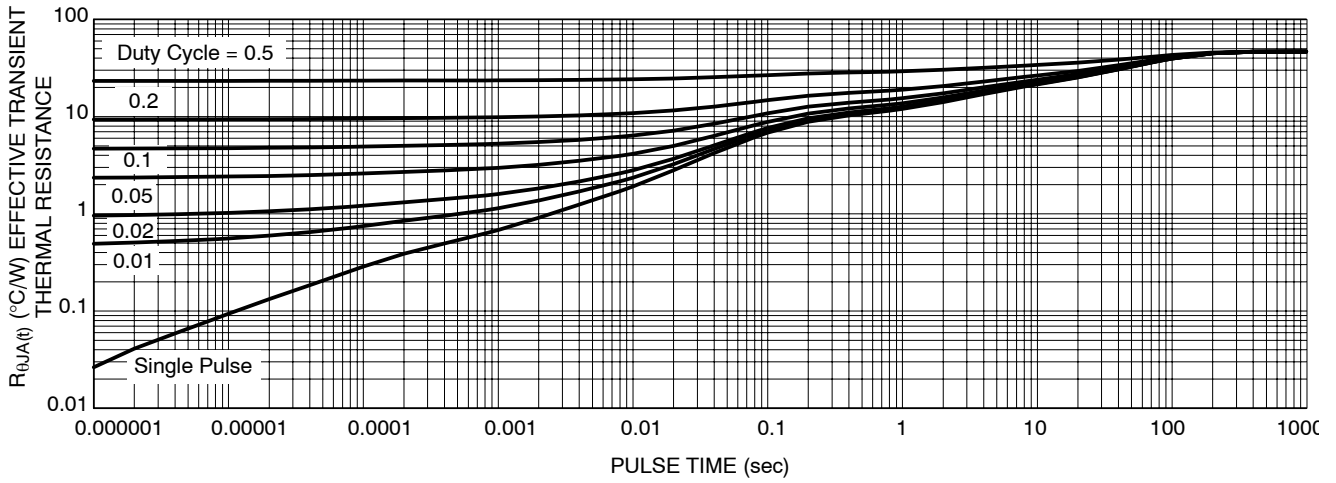


Figure 13. Thermal Response

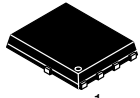
DEVICE ORDERING INFORMATION

Device	Marking	Package	Shipping [†]
NTMFS5844NLT1G	5844NL	DFN5 (Pb-Free)	1500 / Tape & Reel
NVMFS5844NLT1G	V5844L	DFN5 (Pb-Free)	1500 / Tape & Reel
NVMFS5844NLWFT1G	5844LW	DFN5 (Pb-Free)	1500 / Tape & Reel
NVMFS5844NLT3G	V5844L	DFN5 (Pb-Free)	5000 / Tape & Reel
NVMFS5844NLWFT3G	5844LW	DFN5 (Pb-Free)	5000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MECHANICAL CASE OUTLINE

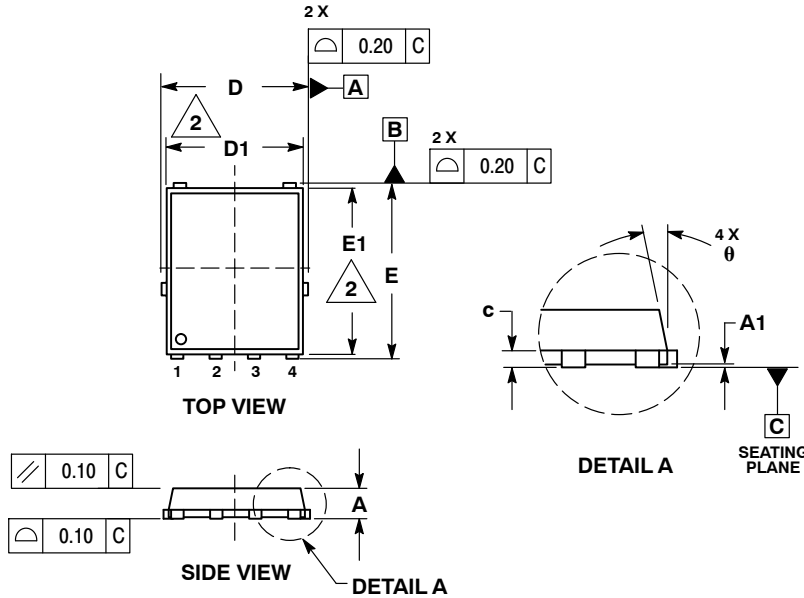
PACKAGE DIMENSIONS



1
SCALE 2:1

DFN5 5x6, 1.27P
(SO-8FL)
CASE 488AA
ISSUE N

DATE 25 JUN 2018

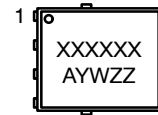


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION D1 AND E1 DO NOT INCLUDE MOLD FLASH PROTRUSIONS OR GATE BURRS.

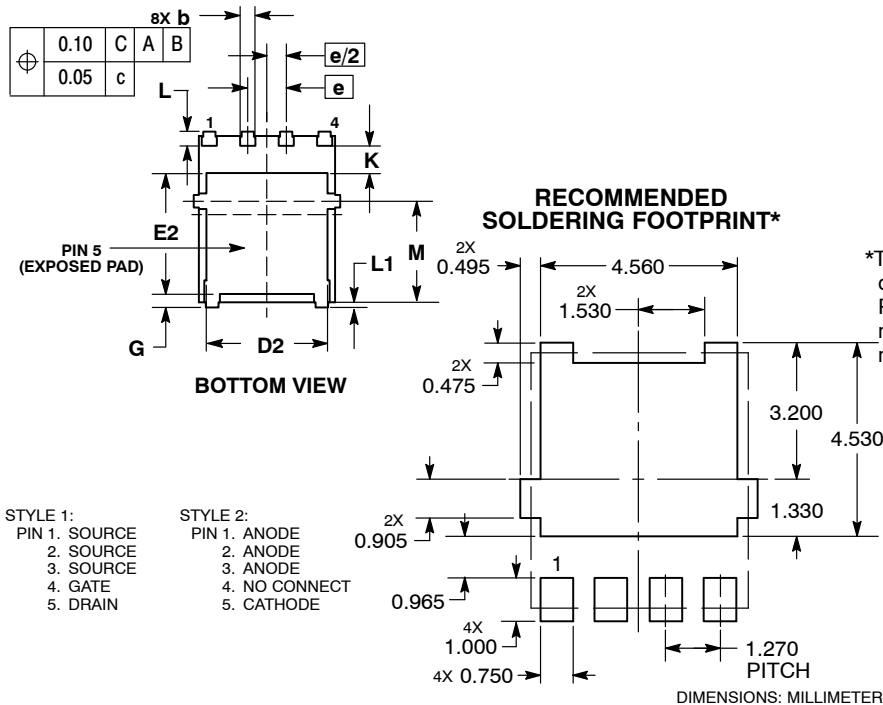
DIM	MILLIMETERS		
	MIN	NOM	MAX
A	0.90	1.00	1.10
A1	0.00	---	0.05
b	0.33	0.41	0.51
c	0.23	0.28	0.33
D	5.00	5.15	5.30
D1	4.70	4.90	5.10
D2	3.80	4.00	4.20
E	6.00	6.15	6.30
E1	5.70	5.90	6.10
E2	3.45	3.65	3.85
e	1.27 BSC		
G	0.51	0.575	0.71
K	1.20	1.35	1.50
L	0.51	0.575	0.71
L1	0.125 REF		
M	3.00	3.40	3.80
θ	0°	---	12°

GENERIC MARKING DIAGRAM*



- XXXXXX = Specific Device Code
- A = Assembly Location
- Y = Year
- W = Work Week
- ZZ = Lot Traceability

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.



STYLE 1:

- PIN 1. SOURCE
- 2. SOURCE
- 3. SOURCE
- 4. GATE
- 5. DRAIN

STYLE 2:

- PIN 1. ANODE
- 2. ANODE
- 3. ANODE
- 4. NO CONNECT
- 5. CATHODE

DIMENSIONS: MILLIMETERS

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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DESCRIPTION:	DFN5 5x6, 1.27P (SO-8FL)	PAGE 1 OF 1

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